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ABSTRACT

A method of fabricating a semiconductor device is advantageous in preventing occurrence of an erroneous short-circuit and a withstand voltage failure in a connection hole and preventing occurrence of a failure at the time of burying a connection hole with a metal. A silicon carbo-nitride film is formed on a conductor or an interconnection of a Damascene structure formed on a silicon substrate (S1), the silicon carbo-nitride film is taken as a side wall or an interlayer insulating film (S2), a silicon oxide film is formed on the silicon carbo-nitride film (S3), the upper side silicon oxide film is etched using the lower side silicon carbo-nitride film as an etching stopper layer (S4), and a connection hole is formed (S5).